

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.



N-Channel SuperFET[®] FRFET[®] MOSFET 600 V, 20 A, 190 mΩ

Features

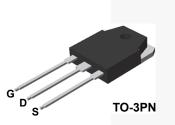
- 650 V @ T_J = 150°C
- Typ. R_{DS(on)} = 150 mΩ
- Fast Recovery Type (Typ. T_{rr} = 160 ns)
- Ultra Low Gate Charge (Typ. Q_g = 75 nC)
- Low Effective Output Capacitance (Typ. Coss(eff.) = 165 pF)
- 100% Avalanche Tested
- RoHS Compliant

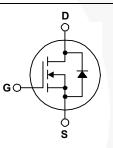
Applications

- LCD / LED / PDP TV
- Solar Inverter
- AC-DC Power Supply

Description

SuperFET[®] MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET FRFET[®] MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings Tc = 25°C unless otherwise noted.

| Symbol | Parameter | | FCA20N60F | Unit | |
|----------------------------------|--|----------|-------------|-----------|--|
| V _{DSS} | Drain-Source Voltage | | 600 | V | |
| ID | Drain Current - Continuous (T _C = 25 - Continuous (T _C = 10 | | 20 12.5 | A A | |
| I _{DM} | Drain Current - Pulsed | (Note 1) | 60 | A | |
| V _{GSS} | Gate-Source voltage | | ± 30 | V | |
| E _{AS} | Single Pulsed Avalanche Energy | (Note 2) | 690 | mJ | |
| I _{AR} | Avalanche Current | (Note 1) | 20 | A | |
| E _{AR} | Repetitive Avalanche Energy | (Note 1) | 20.8 | mJ | |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 50 | V/ns | |
| P _D | Power Dissipation (T _C = 25°C) - Derate . bove 25°C | | 208 1.67 | W W/°C | |
| T _{J,} T _{STG} | Operating and Storage Temperature Range | | -55 to +150 | °C | |
| Τ _L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | | 300 | °C | |

Thermal Characteristics

| Symbol | Parameter | FCA20N60F | Unit | |
|-----------------|---|-----------|------|--|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 0.6 | °C/W | |
| R_{\thetaJA} | Thermal Resistance, Junction-to-Ambient, Max. | 40 | °C/W | |

May 2014

| Part Number Top Ma | | Top Mark | Package | Packing Method | Reel Size | Ta | pe Width | ו Qu | antity | |
|---|---|-------------------------|--|--|-----------|------|----------|-----------|----------|--|
| FCA20 | FCA20N60F FCA20N60F | | TO-3PN | TO-3PN Tube N/A | | N/A | | 30 | 30 units | |
| =lectric: | al Chara | acteristics T - 200 | C uploss otherwi | a noted | | | | | | |
| Symbol | ectrical Characteristics T _C = 25°C unle mbol Parameter | | | Conditions | | Min. | Тур. | Max. | Unit | |
| Off Charac | teristics | | | | | | | | <u> </u> | |
| BV _{DSS} | Drain-Sour | ce Breakdown Voltage | V _{GS} = | V _{GS} = 0 V, I _D = 250 μA, T _J = 25°C | | | | | V | |
| | | | V _{GS} = | $V_{GS} = 0 V, I_D = 250 \mu A, T_J = 150^{\circ}C$ | | | 650 | | V | |
| ΔΒV _{DSS} / ΔΤ _J | Breakdown Voltage Temperature Coefficient | | I _D = 28 | $I_D = 250 \ \mu$ A, Referenced to 25°C | | | 0.6 | | V/°C | |
| BV _{DSS} | Drain-Sour Voltage | ce Avalanche Breakdow | anche Breakdown $V_{GS} = 0 V, I_D = 20 A$ | | | 700 | | V | | |
| I _{DSS} | Zero Gate Voltage Drain Current | | | $V_{DS} = 600 V, V_{GS} = 0 V,$ $V_{DS} = 480 V, T_{C} = 125^{\circ}C$ | | | | 10 100 | μΑ μΑ | |
| I _{GSSF} | Gate-Body | Leakage Current, Forwa | ard V _{GS} = | 30 V, V _{DS} = 0V | | | | 100 | nA | |
| I _{GSSR} | Gate-Body | Leakage Current, Reve | rse V _{GS} = | -30 V, V _{DS} = 0V | | | | -100 | nA | |
| On Charac | teristics | | | | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage $V_{DS} = V_{GS}, I_D =$ | | V _{GS} , I _D = 250 μA | | 3.0 | | 5.0 | V | | |
| R _{DS(on)} | Static Drain-Source On-Resistance | | V _{GS} = | V _{GS} = 10 V, I _D = 10 A | | | 0.15 | 0.19 | Ω | |
| 9 _{FS} | Forward Tr | ransconductance | V_{DS} = | 40 V, I _D = 10 A | | | 17 | | S | |
| Dynamic C | haracterist | ics | | | | | | | | |
| C _{iss} | Input Capa | citance | | $V_{DS} = 25 V, V_{GS} = 0 V,$ f = 1.0 MHz | | | 2370 | 3080 | pF | |
| C _{oss} | Output Ca | pacitance | f = 1.0 | | | | 1280 | 1665 | pF | |
| C _{rss} | Reverse T | ransfer Capacitance | | | | | 95 | | pF | |
| C _{oss} | Output Ca | pacitance | V _{DS} = | V_{DS} = 480 V, V_{GS} = 0 V, f = 1.0 MHz | | | 65 | 85 | pF | |
| C _{oss} eff. | Effective Output Capacitance | | V _{DS} = | V_{DS} = 0 V to 400 V, V_{GS} = 0 V | | | 165 | | pF | |
| Switching | Characteris | tics | | | | | | | | |
| t _{d(on)} | Turn-On D | elay Time | | $\label{eq:VDD} \begin{array}{c} V_{DD} = 300 \text{ V}, \text{ I}_{D} = 20 \text{ A}, \\ R_{G} = 25 \Omega \end{array}$ | | | 62 | 135 | ns | |
| t _r | Turn-On R | ise Time | R _G = 2 | | | | 140 | 290 | ns | |
| t _{d(off)} | Turn-Off D | elay Time | | | | | 230 | 470 | ns | |
| t _f | Turn-Off Fa | all Time | | | | | 65 | 140 | ns | |
| Qg | Total Gate | Charge | | $V_{DS} = 480 \text{ V}, \text{ I}_{D} = 20 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4) | | | 75 | 98 | nC | |
| Q _{gs} | Gate-Sour | ce Charge | V _{GS} = | | | | 13.5 | 18 | nC | |
| Q _{gd} | Gate-Drain | Charge | | | | | 36 | | nC | |
| Drain-Sour | ce Diode C | haracteristics and Max | imum Rating | IS | | | | 1 | <u> </u> | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | | | | 20 | Α | | | |
| I _{SM} | Maximum | Pulsed Drain-Source Dic | de Forward (| Current | | | | 60 | А | |
| V _{SD} | Drain-Sour | ce Diode Forward Voltag | ge V _{GS} = | 0 V, I _S = 20 A | | | | 1.4 | V | |
| t _{rr} | | ecovery Time | V _{GS} = | $V_{GS} = 0 V, I_{S} = 20 A,$ dI _F /dt = 100 A/µs | | | 160 | | ns | |
| Q _{rr} | | ecovery Charge | dl _F /dt | | | | 1.1 | | μC | |

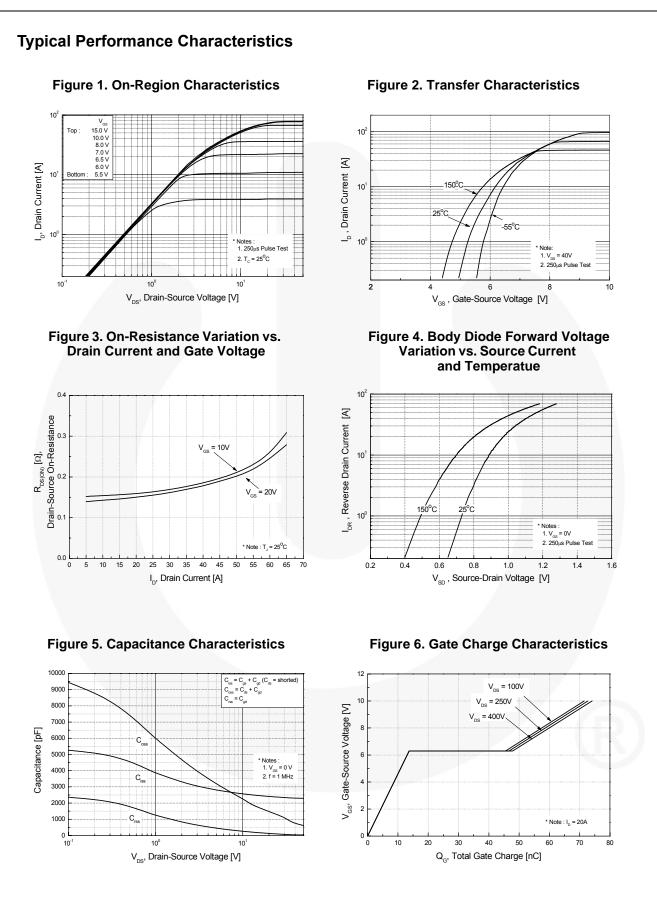
1. Repetitive rating: pulse-width limited by maximum junction temperature.

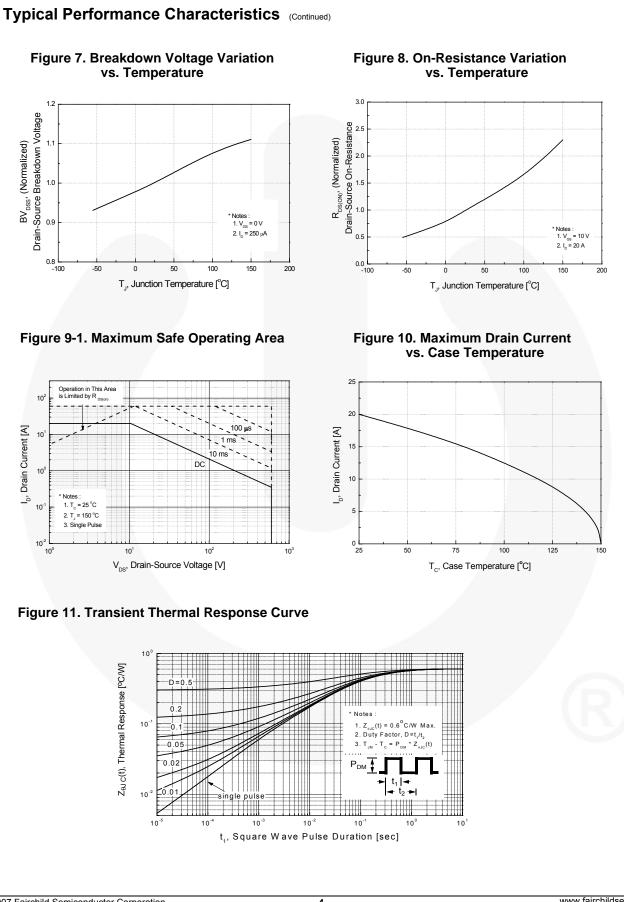
2. I_{AS} = 10 A, V_{DD} = 50 V, R_{G} = 25 $\Omega,$ starting T_{J} = 25°C.

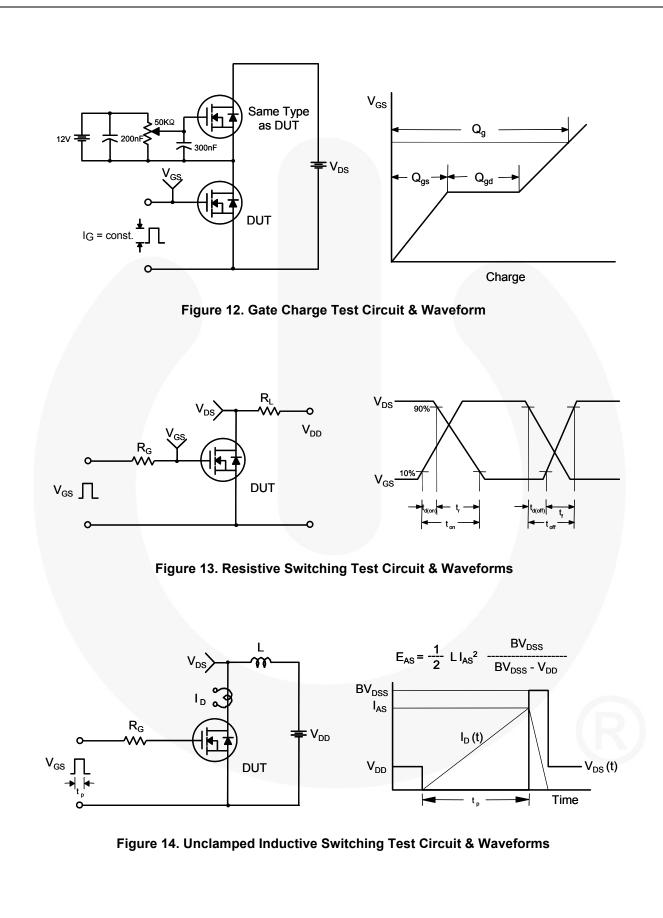
3. $I_{SD} \le 20$ A, di/dt ≤ 1200 A/µs, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.

4. Essentially independent of operating temperature typical characteristics.

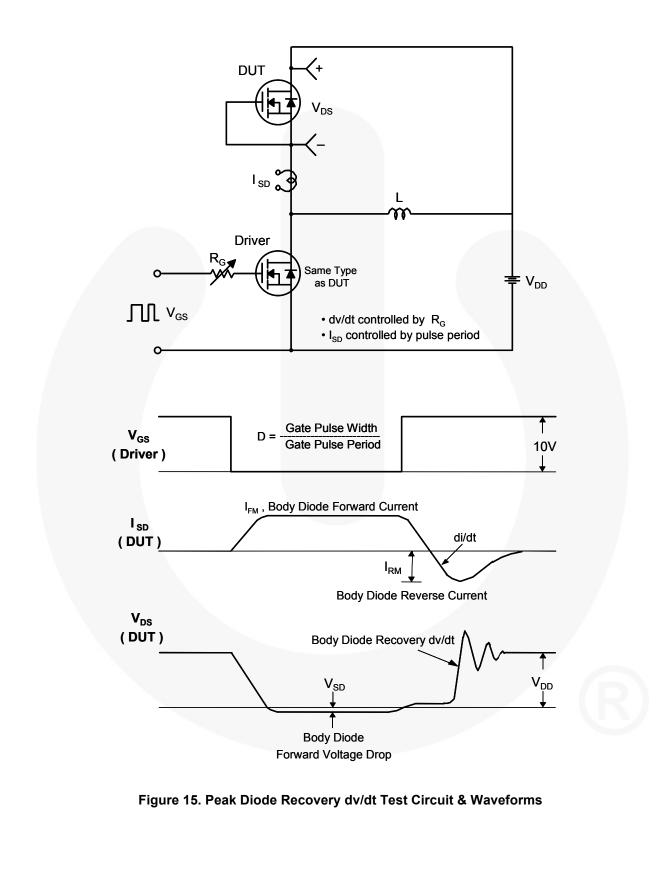
FCA20N60F — N-Channel SuperFET[®] FRFET[®] MOSFET



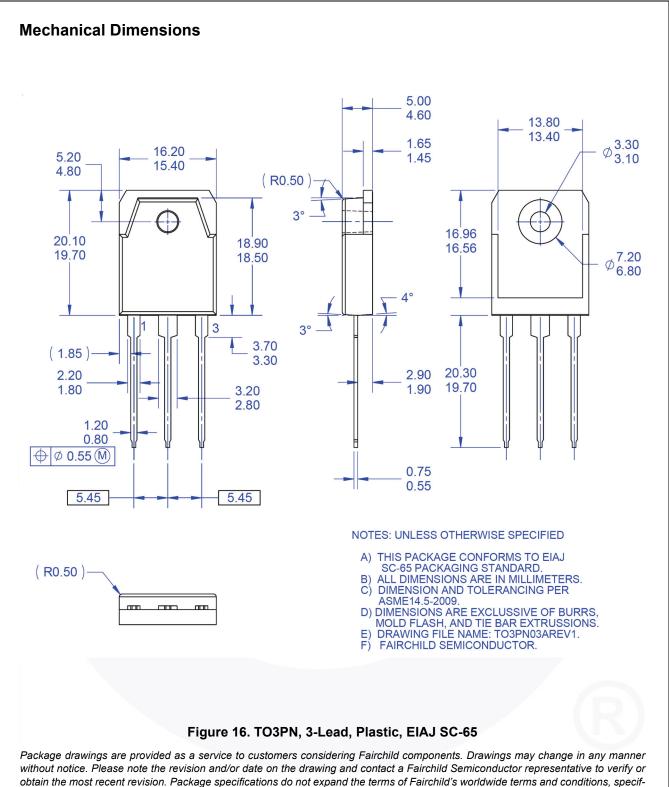




FCA20N60F — N-Channel SuperFET[®] FRFET[®] MOSFET



FCA20N60F — N-Channel SuperFET[®] FRFET[®] MOSFET



ically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT3PN-003



ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UF0-7B